a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein a portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein a portion which said second conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Cancel Claim 5.

6. **(Thrice Amended)** A ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with said gate insulating film and top and side surfaces of said first conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein a portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein the portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT does not overlap said first source and drain regions;

wherein a portion which said second conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Cancel Claim 10.

11. **(Thrice Amended)** A ferroelectric liquid crystal display device having an n-channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

a first gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a pair of LDD regions and first source and drain regions;

wherein said first gate electrode partially overlaps said pair of LDD regions, and

said p-channel TFT comprising:

a second gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film interposed therebetween, said second semiconductor layer comprising a second channel formation region and second source and drain regions being in contact with said second channel formation region,

wherein said second gate electrode partially overlaps said second source and drain regions, and

wherein a wiring is connected to at least one of said second source and drain regions.

14. **(Thrice Amended)** A goggle type display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with said gate insulating film and top and side surfaces of said first conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein a portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein a portion which said second conductive layer is in contact with said gate insulating film in said p-channel TFT is partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Cancel Claim 18.

19. **(Thrice Amended)** A goggle type display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with said gate insulating film and top and side surfaces of said first conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein a portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein the portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT does not overlap said first source and drain regions;

wherein a portion which said second conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Cancel Claim 23.

24. **(Thrice Amended)** A goggle type display device having an n-channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

a first gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a pair of LDD regions and first source and drain regions;

wherein said first gate electrode partially overlaps said pair of LDD regions, and

said p-channel TFT comprising: